

**AMENDMENTS TO THE SPECIFICATION:**

Please replace the paragraph beginning on page 15, line 11 with the following:

[0040] An Over Etch (OE) step after the Main Etch (ME) may affect the composition of the chamber deposits. Table 3 shows the recipes used to study the effects of the OE step. The ME may include  $C_xH_yF_z$   $C_xF_yH_z$  as a component wherein  $x \geq 1$ ,  $y \geq 1$ , and  $z \geq 0$ . An example of representative gas is  $CHF_3$ . The OE may be carried out with a  ~~$C_xH_yF_z$ -free~~  $C_xF_yH_z$ -free gas, e.g.,  $BCl_3$  and/or  $Cl_2$  as components. The wafers used were 50% Open Area Aluminum wafers (10,000 Å A1).

Please replace the paragraph beginning on page 16, line 2 with the following:

[0042] Figure 4 shows that when the base WAC was added after each wafer was processed with ME and OE, almost all of the deposit is eliminated. The amount of Al and F in the chamber deposit is surprisingly decreased with the addition of the  ~~$C_xH_yF_z$ -free~~  $C_xF_yH_z$ -free OE step even without WAC. The OE step may eliminate the Al and F in the deposit, leaving mostly volatile substance. This was observed at all three test piece locations and suggests that the ME and OE process is efficient at removing both Al and F deposits and volatile matter.